

6 deep source and drain regions with dopants of the first conductivity type,
7 wherein the gate structure is between the source and drain regions, wherein the
8 drain extension is deeper than the source extension.

1 32. (Once Amended) The integrated circuit of claim 31, further
2 comprises:

3 providing a pair of spacers abutting lateral sides of the gate structure;
4 and providing a deep source/drain implant at the source location and the
5 drain location

36. (Once Amended) The integrated circuit of claim 31, wherein the deep source and deep drain regions have a concentration of dopants between 10^{19} and 10^{20} dopants per cc, the source extension has a concentration of dopants between 5×10^{19} and 10^{20} dopants per cc, and the drain extension has a concentration of dopants between 1×10^{19} and 5×10^{19} dopants.

1 37. (Once Amended) The integrated circuit of claim 31, wherein the
2 first conductivity type is P-type or N-type.

REMARKS

2 Applicant respectfully requests reconsideration of the present application
3 in view of the foregoing amendments and in view of the reasons which follow.

4 Claims 18-37 are rejected. Claims 31, 33, 36, and 37 have been amended.

5 Therefore, claims 18-37 remain pending in the application.

6 Claims 31 and 32 have been amended to correct typographical errors.

7 Claim 37 has been amended to increase its breadth. The amendments to claims
8 31, 32, and 37 are not made in a limiting fashion and they are not made for
9 patentability. Claim 37 is amended to include limitations related to the
10 concentration of dopants in the recited structures. No new matter is added in
11 the amendments to claims 31, 32, and 36 and 37.

12 As a preliminary matter, the Examiner objected to the drawings. Formal
13 drawings will be provided when a Notice of Allowance is received.